

External_Type	Material_Group	Substances	CAS_Number	Mass	Mass_Percentage_in_Leaf	Massmg
Die		Lead Dioxide (PbO2)	1309-60-0	0.00192	0.74	0.11544
	Doped silicon	Silicon (Si)	7440-21-3	0.25793	99.26	15.48456
Subtotal				0.25985	100	15.6
Post-plating	Lead alloy	Tin (Sn)	7440-31-5	0.45308	100.0	27.2
Subtotal				0.45308	100	27.2
Lead Frame	Copper alloy	Phosphorous (P)	7723-14-0	0.02	0.03	1.20057
	Copper alloy	Iron (Fe)	7439-89-6	0.06666	0.1	4.0019
	Copper alloy	Copper (Cu)	7440-50-8	66.57501	99.87	3,996.69753
Subtotal				66.66167	100	NaN
Mould Compound	Polymer	Phenol Formaldehyde resin (generic)	9003-35-4	2.08817	6.5	125.359
	Polymer	Epichlorohydrin/o-Cresol/Formaldehyde polymer (generic)	29690-82-2	5.14011	16.0	308.576
	Filler	Silica fused	60676-86-0	22.80922	71.0	1,369.306
	Flame retardant	Metal hydroxide		2.08817	6.5	125.359
Subtotal				32.12567	100	NaN
Solder Wire	Lead alloy	Tin (Sn)	7440-31-5	0.01916	5.0	1.15
	Lead alloy	Silver (Ag)	7440-22-4	0.00958	2.5	0.575
	Lead alloy	Lead (Pb)	7439-92-1	0.35439	92.5	21.275
Subtotal				0.38313	100	23
Wire	Pure metal	Aluminium (Al)	7429-90-5	0.1166	100.0	7
Subtotal				0.1166	100	7
Total				100	100	NaN

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